
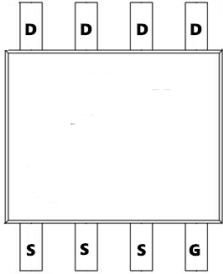


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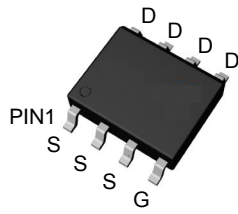
N-Channel Enhancement Mosfet

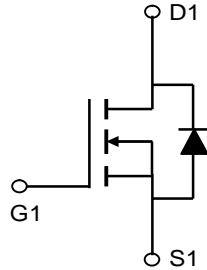
<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 20V$ $I_D = 10A$</p> <p>$R_{DS(ON)} = 12m\ \Omega$ (typ.) @ $V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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PIN1

S:SOP-8L





Marking: 10N02 OR 2010

Absolute Maximum Rating ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	10	A
Pulsed Drain Current ¹	I_{DM}	20	A
Power Dissipation	P_D	2.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	90	$^\circ C/W$

TMN2012S

N-Channel Enhancement Mosfet

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} = 0 V, I _D = 250μA	20	-	-	V
Gate Leakage Current	I_{GSS}	V _{GS} = ±12V, V _{DS} = 0 V	-	-	±100	nA
Drain Cut-off Current	I_{DSS}	V _{DS} = 20V, V _{GS} = 0 V	-	-	1	μA
Gate Threshold Voltage	V_{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	0.45	0.7	1	V
Drain-Source On-State Resistance ³	R_{DS(on)}	V _{GS} = 4.5V, I _D = 5A	-	12	15	mΩ
		V _{GS} = 2.5V, I _D = 4.7A	-	17	21	
		V _{GS} = 1.8V, I _D = 4.3A	-	28	50	
Dynamic Characteristics⁴						
Input Capacitance	C_{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz	-	700	-	pF
Output Capacitance	C_{oss}		-	120	-	
Reverse Transfer Capacitance	C_{rss}		-	105	-	
Switching Characteristics⁴						
Total Gate Charge	Q_g	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 5A	-	10.5	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	
Gate-Drain Charge	Q_{gd}		-	2.5	-	
Turn-On Time	t_{d(on)}	V _{GEN} = 5V, V _{DD} = 10V, I _D = 5A, R _G = 3Ω,	-	10	-	ns
Rise Time	t_r		-	20	-	
Turn-Off Time	t_{d(off)}		-	32	-	
Fall Time	t_f		-	12	-	
Source-Drain Diode Characteristics						
Body Diode Voltage ³	V_{SD}	I _S = 4A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	I_S		-	-	10	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

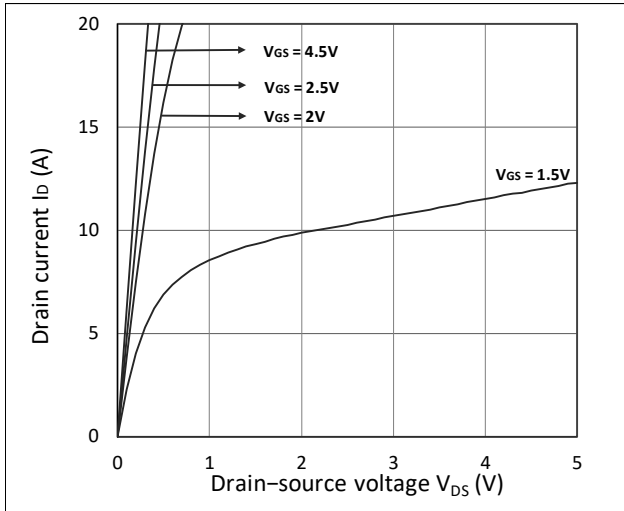


Figure 1. Output Characteristics

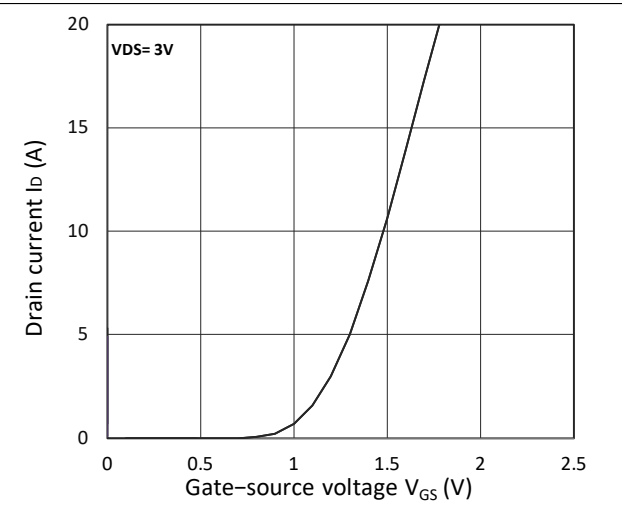


Figure 2. Transfer Characteristics

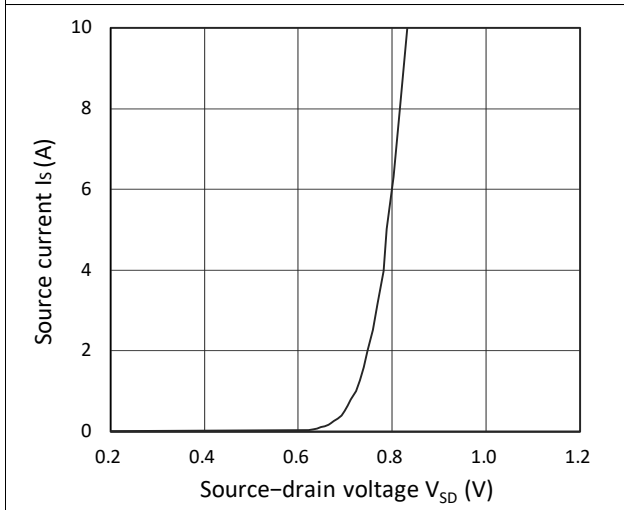


Figure 3. Forward Characteristics of Reverse

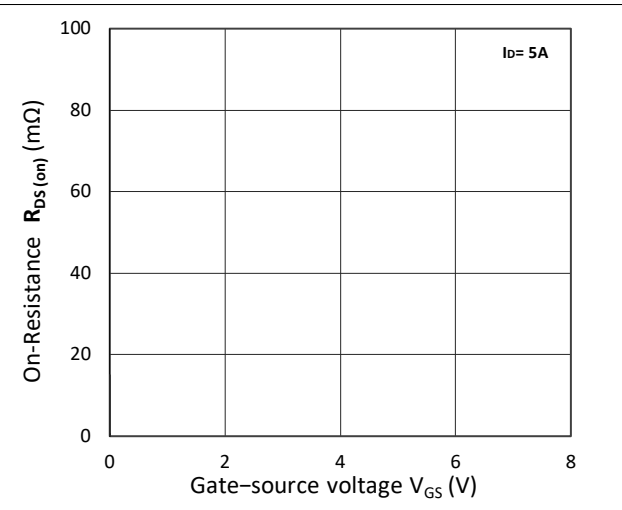


Figure 4. $R_{DS(on)}$ vs. V_{GS}

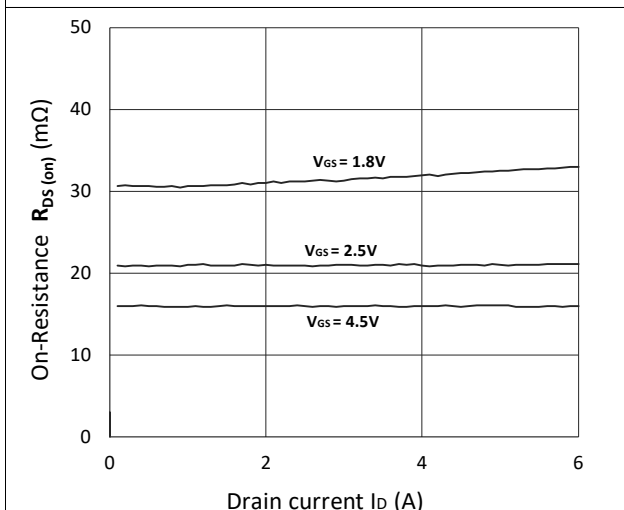


Figure 5. $R_{DS(on)}$ vs. I_D

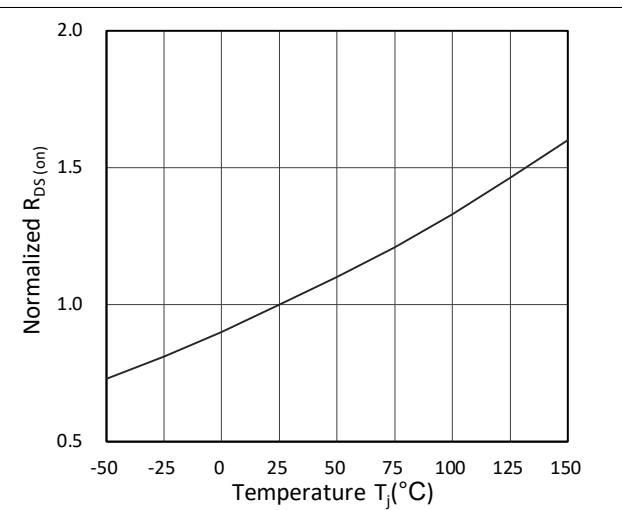


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature



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N-Channel Enhancement Mosfet

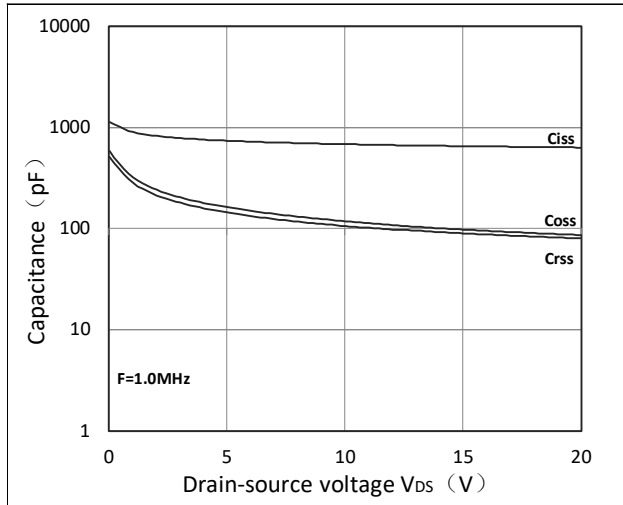


Figure 7. Capacitance Characteristics

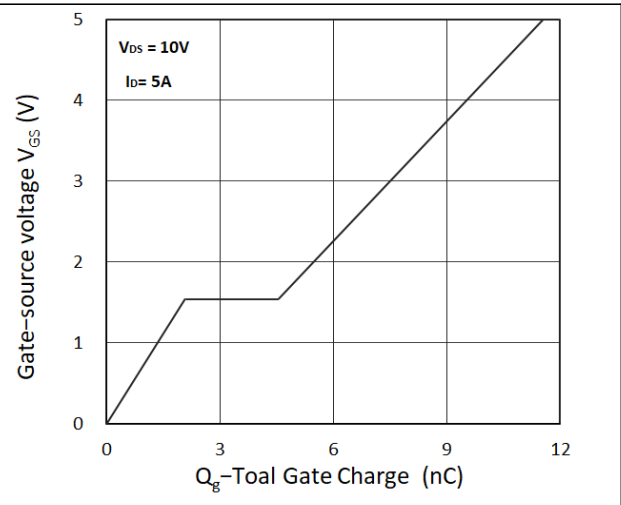
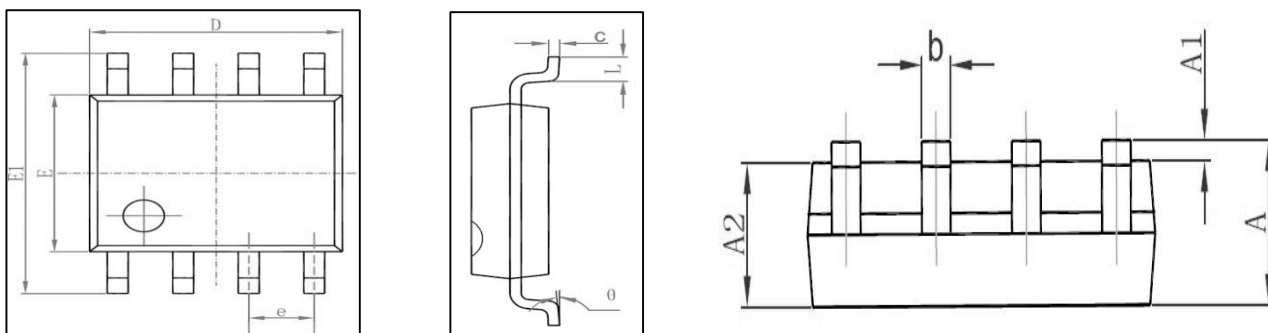
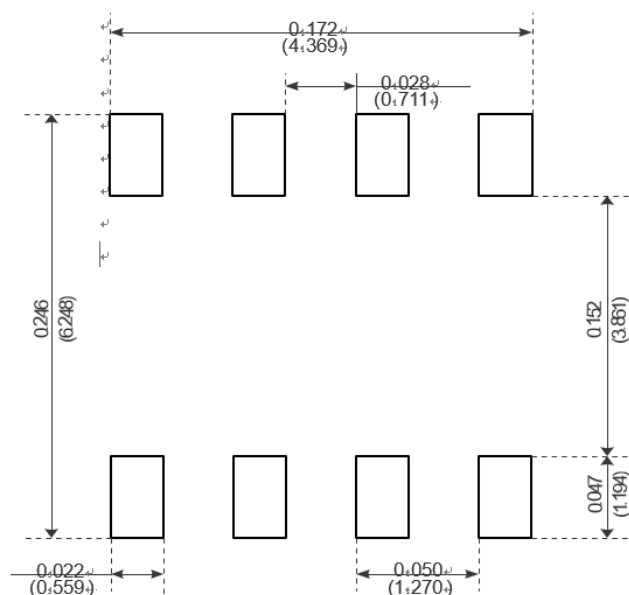


Figure 8. Gate Charge Characteristics

Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads